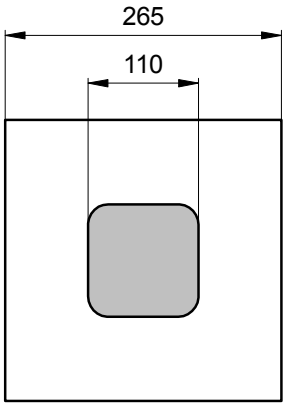
LED - Chip ELC-645-13

21.11.2007 rev. 06

Radiation	Type	Technology	Electrodes
Red	Standard	AlInGaP/GaAs	P (anode) up



typ. dimensions (µm)

typ. thickness
260 (±20) µm

cathode
gold alloy, 0.5 µm

anode
gold alloy, 1.5 µm

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.9	2.3	V
Reverse voltage	I_R = 10 µA	V_R	5			V
Radiant power[1]	I_F = 20 mA	Φ_e	1.2	2.0		mW
Radiant power[2]	I_F = 20 mA	Φ_e		4.0		mW
Luminous intensity[1]	I_F = 20 mA	I_v	40	70		mcd
Luminous intensity[2]	I_F = 20 mA	I_v		140		mcd
Peak wavelength	I_F = 20 mA	λ_P	635	645	655	nm
Dominant wavelength	I_F = 20 mA	λ_D		632		nm
Spectral bandwidth at 50%	I_F = 20 mA	$\Delta\lambda_{0.5}$		18		nm
Switching time	I_F = 20 mA	t_r, t_f		15		ns

[1]Measured on bare chip on TO-18 header with *EPIGAP* equipment
[2]Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	I_V(typ) [mcd]	V_F(typ) [V]	Quantity
ELC-645-13				

Packing: Chips on adhesive film with wire-bond side on top

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